

自主封測 品質把控 售後保障

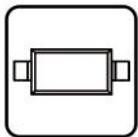
WEB | WWW.TDSEMIC.COM



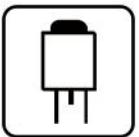
電源管理



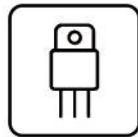
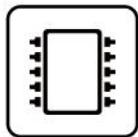
顯示驅動



二三極管 LDO穩壓器



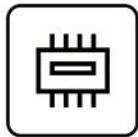
觸摸芯片



MOS管



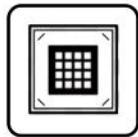
運算放大器



存儲芯片



MCU



串口通信

SS54C-TD

產品規格說明書

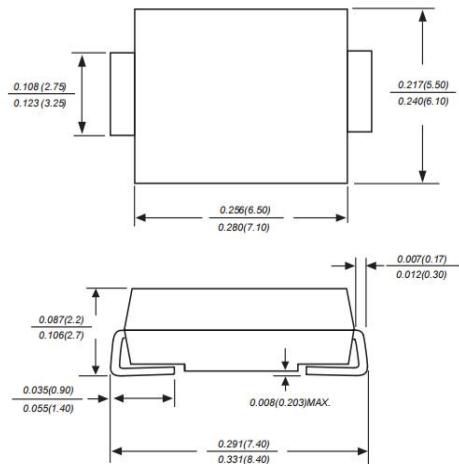
SS52 THRU SS520

SURFACE MOUNT SCHOTTKY BARRIER RECTIFIER

Reverse Voltage - 20 to 200 Volts Forward Current - 5.0 Amperes

SMC

DO-214AB



Dimensions in inches and (millimeters)

FEATURES

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- For surface mounted applications
- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- Built-in strain relief, ideal for automated placement
- High forward surge current capability
- High temperature soldering guaranteed: 250°C/10 seconds at terminals

MECHANICAL DATA

Case: JEDEC DO-214AB molded plastic body

Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any

Weight: 0.008 ounce, 0.217 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

	SYMBOLS	SS52	SS53	SS54	SS55	SS56	SS59	SS510	SS515	SS520	UNITS				
Maximum repetitive peak reverse voltage	V_{RRM}	20	30	40	50	60	90	100	150	200	VOLTS				
Maximum RMS voltage	V_{RMS}	14	21	28	35	42	63	70	105	140	VOLTS				
Maximum DC blocking voltage	V_{DC}	20	30	40	50	60	90	100	150	200	VOLTS				
Maximum average forward rectified current at T_L (see fig.1)	$I_{(AV)}$	5.0								Amps					
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	150.0								Amps					
Maximum instantaneous forward voltage at 5.0A	V_F	0.45	0.55	0.70			0.85			Volts					
Maximum DC reverse current $T_A=25^\circ C$ at rated DC blocking voltage $T_A=100^\circ C$	I_R	0.5				0.1				mA					
		20													
Typical junction capacitance (NOTE 1)	C_J	800								pF					
Typical thermal resistance (NOTE 2)	R_{qJA}	40.0								$^\circ C/W$					
Operating junction temperature range	T_J	-65 to +125			-65 to +150					$^\circ C$					
Storage temperature range	T_{STG}	-65 to +150								$^\circ C$					

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
2. P.C.B. mounted with 0.6x0.6" (16x16mm) copper pad areas

AVERAGE FORWARD RECTIFIED CURRENT,
AMPERES

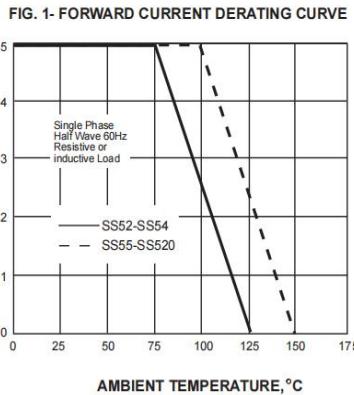
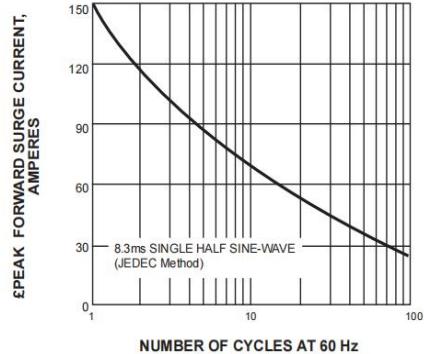
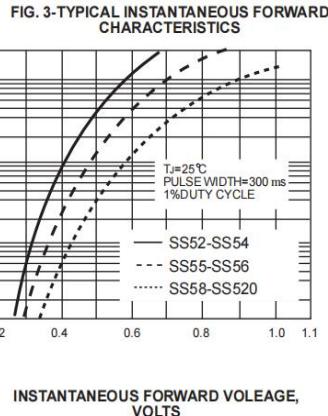


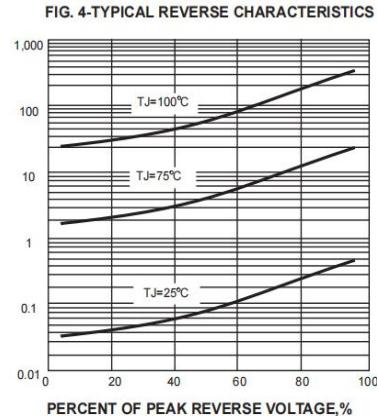
FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT



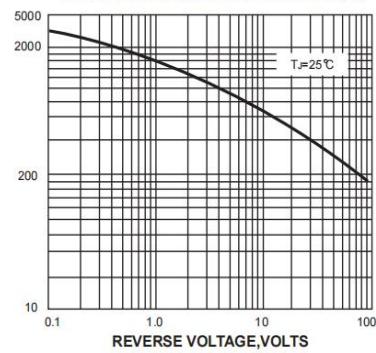
INSTANTANEOUS FORWARD CURRENT, AMPERES



INSTANTANEOUS REVERSE CURRENT,
MILLIAMPERES



JUNCTION CAPACITANCE, pF



TRANSIENT THERMAL IMPEDANCE,
°C/W

